

Features

2005.1.6

- . Especially suited for use Electret Condenser Microphone. (ECM)
- . Excellent voltage characteristics.
- . Excellent transient characteristics.

Adoption Maximum Ratings/Ta=25

Event	Code	Set	Unit
Gate to Drain Voltage	V _{GDO}	-20	V
Drain Current	I _D	1	m A
Gate Current	I _G	10	m A
Allowable Power Dissipation	P _D	100	m W
Junction Temperature	T _j	150	
Storage Temperature	T _{stg}	-55 to +150	

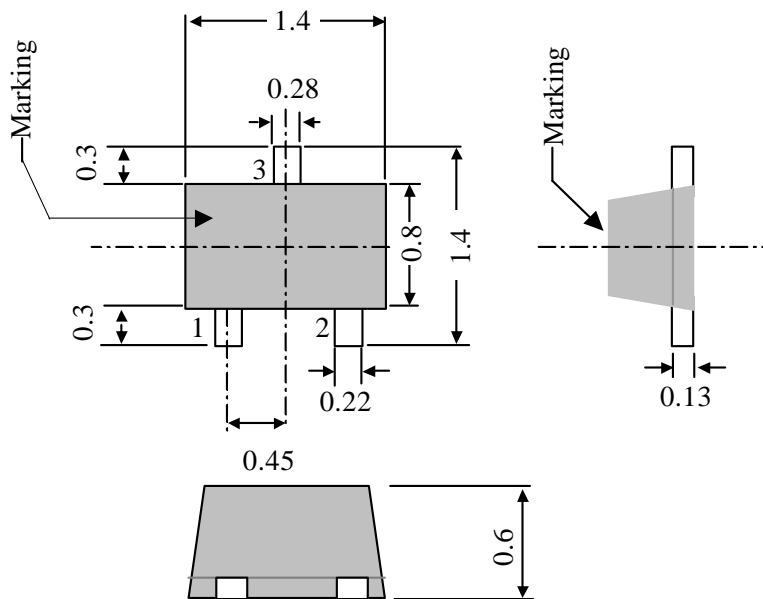
Electrical Characteristics/Ta=25

Event	Code	Set	MIN	TYP	MAX	Unit
G-D Breakdown Voltage	V _{GDO}	I _G =-100uA	-20			V
Drain Current	I _{DSS}	V _{DS} = 5.0 V , V _{GS} = 0 V	140	250	350	u A
Gate off Voltage	V _{GS(OFF)}	V _{DS} = 5.0 V , I _D = 1 u A	-0.2	-0.6	-1.2	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = 5.0 V , V _{GS} = 0 , f = 1KHz	0.5	1.2		m S
Input Capacitance	C _{iss}	V _{DS} = 5.0 V , V _{GS} = 0 , f = 1MHz		3.5		p F
Reverse Transfer Capacitance	C _{rss}	V _{DS} = 5.0 V , V _{GS} = 0 , f = 1MHz		0.65		p F

The FJT TF202-T is classified by I_{DSS} as follows :(unit:uA)

Marking	E4	E5
I _{DSS}	140to240	210to350

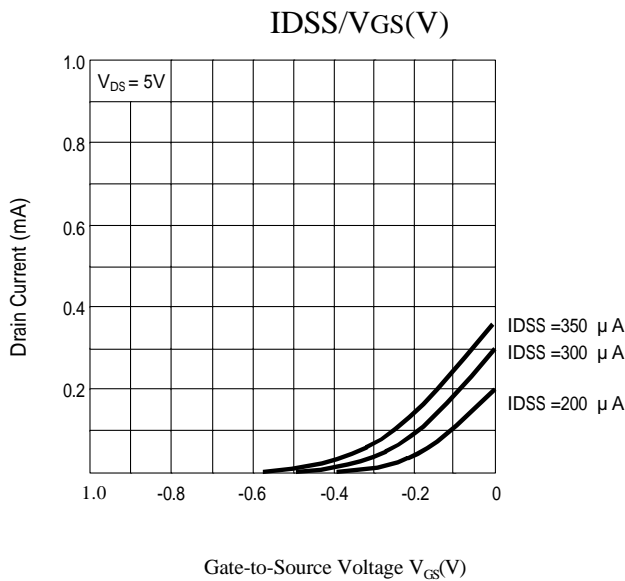
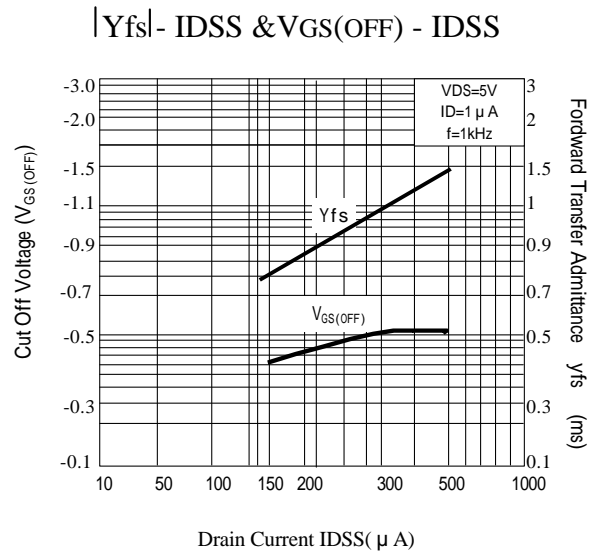
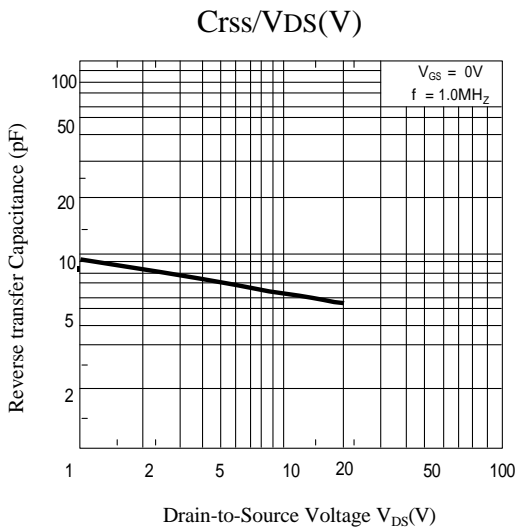
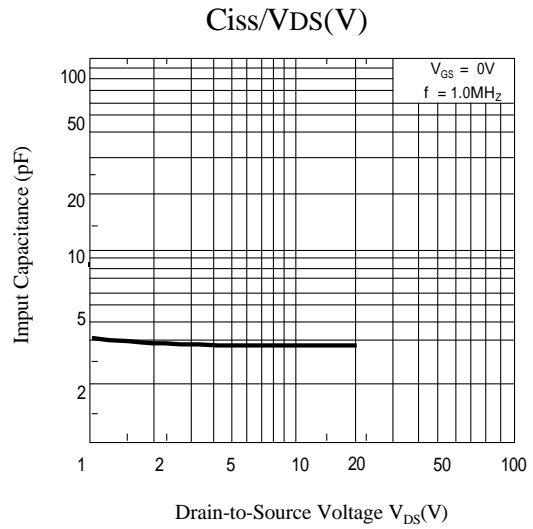
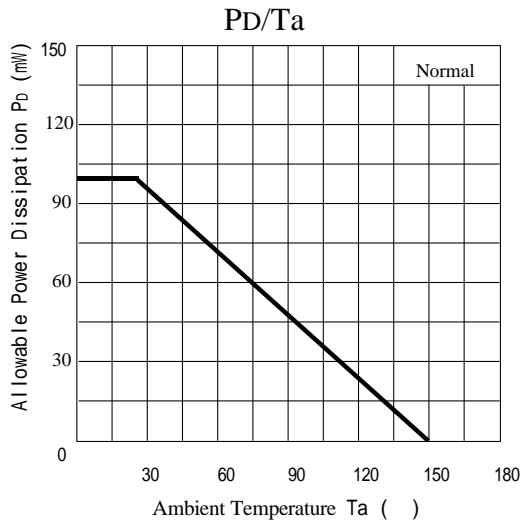
Package Dimensions

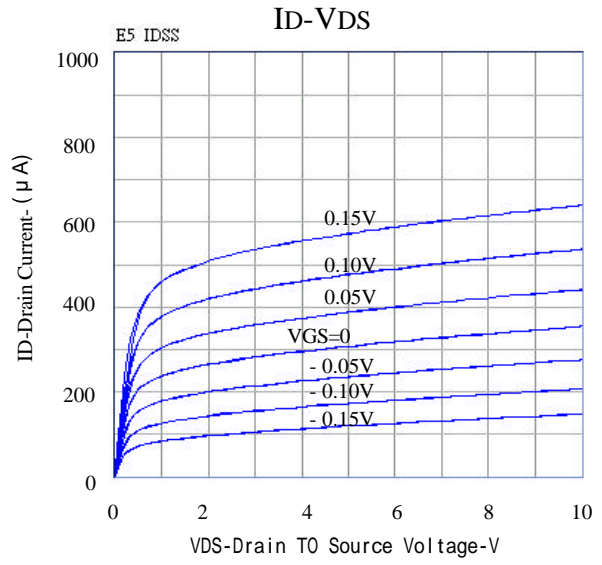
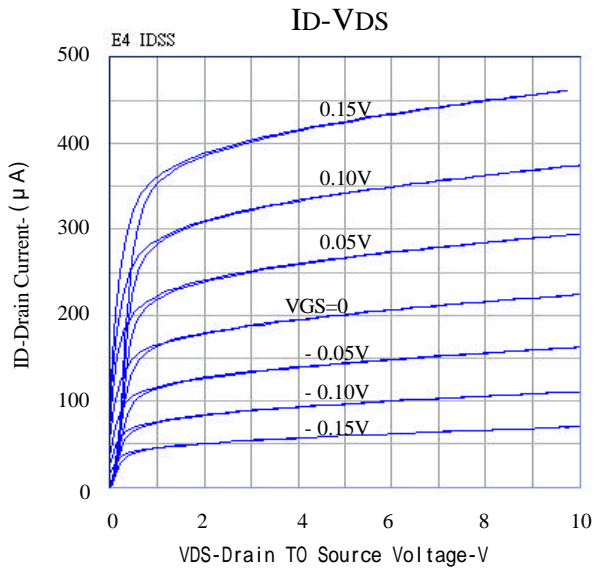


1 : Drain
 2 : Source
 3 : Gate
 SOT-113(unit:mm)

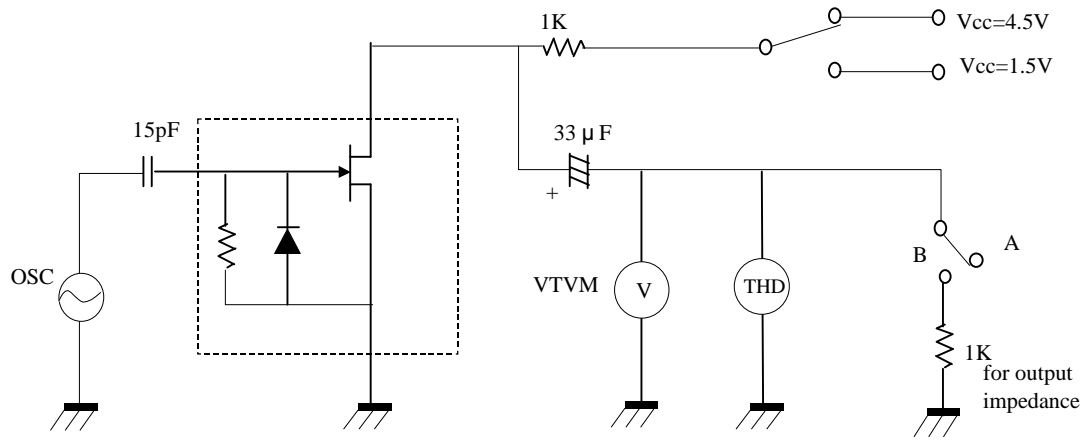
Remarks :

- . Patent No : Taiwan 90205055、090209174 ; China 01218819.0、01227314.7 ; Japan 2001-2220.





TEST CIRCUIT (Ta=25)



PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Voltage Gain	Gv	V _{IN} =10mV, f=1KHz		-3.0		dB
Reduced Voltage Characteristic	G _{VV}	V _{IN} =10mV, f=1KHz, V _{CC} =4.5V 1.5V		-1.2	-3.5	dB
Frequency Characteristic	G _{vf}	f=1KHz to 110Hz			-1.0	dB
Input Resistance	Z _{IN}	f=1KHz	25			M
Output Resistance	Z _o	f=1KHz		1000		
Total Harmonic Distortion	THD	V _{IN} =30mV, f=1KHz		1.0		%
Output Noise Voltage	V _{No}	V _{IN} =0, A CURVE			-110	dB